GD103SD

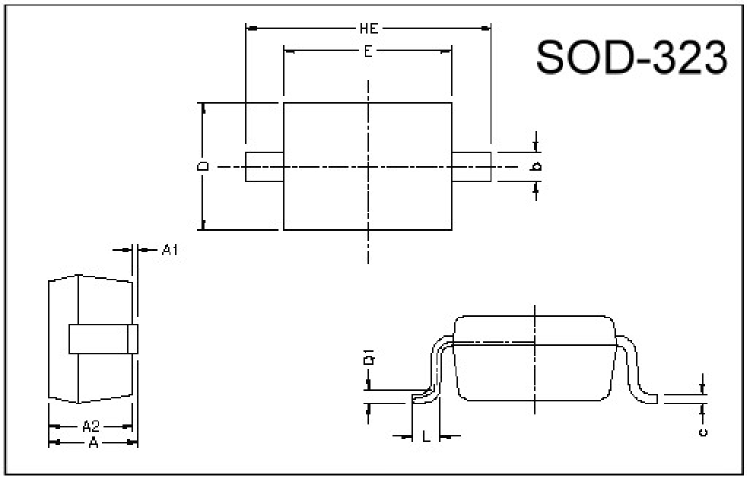
SURFACE MOUNT, SCHOTTKY BARRIER DIODE

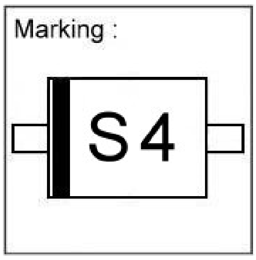
VOLTAGE 40V, CURRENT 350mA

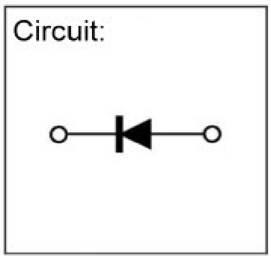
Description

The GD103SD is designed for low forward voltage drop, guard ring construction for transient protection, negligible reverse recovery time and low reverse capacitance.

Package Dimensions







REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.85	1.05			
A1	0	0.10	L	0.20	0.40
A2	0.80	1.00	b	0.25	0.40
D	1.15	1.45	c	0.10	0.18
E	1.60	1.80			
HE	2.30	2.70	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Storage Temperature	Tstg	-65 ~ +125	℃
Peak Repetitive Reverse Voltage	V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Forward Continuous Current	I_F	350	mA
Repetitive Peak Forward Current(t≦1.0s)	I_{FRM}	1.5	A
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	℃/W
Total Power Dissipation at Ta = 25℃	PD	225	mW

Characteristics at Ta = 25℃

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	40	-	-	V	IR=10μA
Forward Voltage	$V_{F(1)}$	-	-	370	mV	IF=20mA
	$V_{F(2)}$	-	-	600	mV	IF=200mA
Reverse Leakage Current	I_R	-	-	5.0	μA	VR=30V
Total Capacitance	C_T	-	5.0	-	pF	VR=0V, f=1MHz
Reverse Recover Time	Trr	-	10	-	ns	IF=IR=200mA, IR(Rec)=20mA, RL=100Ω

Characteristics Curve

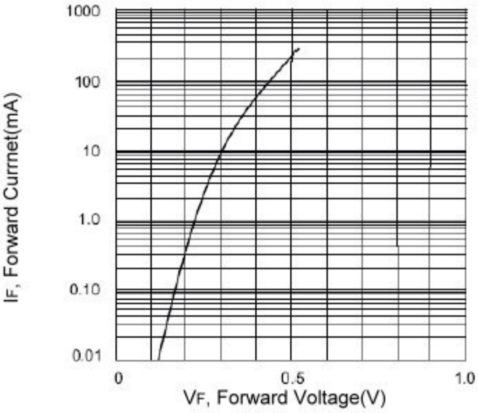


Fig. 1 Typical Forward Characteristics

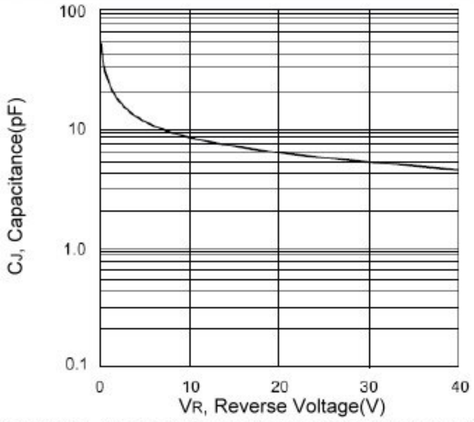


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage